IN THE CLAIMS

1 (Original). A method comprising:

forming a source drain extension by implanting boron, carbon, and fluorine.

2 (Original). The method of claim 1 including implanting carbon to a depth deeper than the boron implant.

3 (Original). The method of claim 2 including implanting fluorine to a depth deeper than the boron implant.

4 (Original). The method of claim 1 including implanting carbon at an energy of about 6 KeV.

5 (Original). The method of claim 4 including implanting carbon at a dose of about 1E15 atoms/cm^2.

6 (Original). The method of claim 1 including performing a Halo implant before the implanting boron.

7 (Original). A method comprising:

implanting boron and fluorine to form a source drain extension; and

implanting an additional species to reduce transient enhanced diffusion of boron.

8 (Original). The method of claim 7 including implanting carbon as said additional species.

9 (Original). The method of claim 8 including implanting carbon to a depth deeper than the boron implant.

10 (Original). The method of claim 9 including implanting fluorine to a depth deeper than the boron implant.

11 (Original). The method of claim 8 including implanting carbon at an energy of about 6 KeV.

12 (Original). The method of claim 11 including implanting carbon at a dose of about 1E15 atoms/cm^2.

13 (Original). The method of claim 7 including performing a Halo implant before implanting boron.

14 (Withdrawn). An integrated circuit comprising:

a P-type transistor having a source drain extension including carbon and boron.

15 (Withdrawn). The circuit of claim 14 wherein said extension includes fluorine.

16 (Withdrawn). The circuit of claim 14 wherein carbon is deeper than said boron.

17 (Withdrawn). The circuit of claim 14 wherein fluorine is deeper than said boron.

18 (Original). A method comprising:

performing an Arsenic Halo implant before implanting to form P-type source/drain extensions.

19 (Original). The method of claim 18 including forming the P-type source/drain extensions using boron, carbon, and fluorine implants.

20 (Original). The method of claim 18 including implanting carbon to a depth deeper than the boron implant.

21 (Original). The method of claim 20 including implanting fluorine to a depth deeper than the boron implant.